

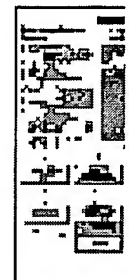
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HATANO MUTSUOKO;  
MIN-HON LEE;  
SEUN JAE MUUN;**Assignee: **REGENTS OF THE UNIV OF CALIFORNIA  
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[News, Profiles, Stocks and More about this company](#)Published / Filed: **2002-04-12 / 2001-08-09**Application Number: **JP2001000241661**IPC Code: **H01L 21/20; H01L 21/268; H01L 21/336; H01L 29/786;**Priority Number: **2000-08-10 US2000000637325**Abstract: **PROBLEM TO BE SOLVED:** To provide a method and an apparatus for forming a polycrystal silicon having large grains from amorphous silicon.**SOLUTION:** A first energy beam is emitted to a layer of a material at a first time point for a first time. A second energy beam is emitted to the layer of the material at a second time point for a second time. Here, the second time point is set after the first time point. The second time is set to the same as or shorter than the first time. Thus, the layer of the material is converted from a first state to a second state.

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